

100V N-Channel Power MOSFET

Pb RoHS

COMI LIANGE

TO-220

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)		$R_{DS(on)}(m\Omega)$	I _D (A)		
	100	5.5 @ V _{GS} =10V	160		

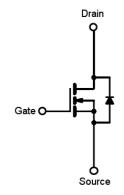
Features

- Advanced Trench Technology
- Low $R_{DS(ON)} 5.5 m\Omega$ (Max.)
- Low gate charge typical @ 154nC (Typ.)
- Low Crss typical @ 260pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM160N10CZ C0	TO-220	50pcs / Tube

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	±20	V	
	T _C =25°C		160		
Continuous Drain Current	T _C =70°C		127	Α	
Continuous Drain Current	T _A =25°C	l _D	14.2		
	T _A =70°C		11.4		
Drain Current-Pulsed Note 1		I _{DM}	620	Α	
Avalanche Current, L=0.5mH		I _{AS} , I _{AR}	40	Α	
Avalanche Energy, L=0.5mH		E _{AS} , E _{AR}	400	mJ	
	T _C =25°C		300		
Mayimya Dayar Dissipation	T _C =70°C		210	W	
Maximum Power Dissipation	T _A =25°C	P_{D}	2.4		
	T _A =70°C		1.68	r	
Storage Temperature Range	·	T _{STG}	-55 to +175	°C	
Operating Junction Temperature Range		TJ	-55 to +175	°C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	R⊖ _{JC}	0.5	°C/W	
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62.5	°C/W	

Notes: Surface mounted on FR4 board t ≤ 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		4.5	5.5	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 30V, I_{D} = 30A,$ $V_{GS} = 10V$	Q_g		154		nC
Gate-Source Charge		Q_{gs}		35		
Gate-Drain Charge		Q_{gd}		40		
Input Capacitance	V _{DS} = 30V, V _{GS} = 0V,	C _{iss}		9840		
Output Capacitance		C_{oss}		750		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		260		
Switching						
Turn-On Delay Time		$t_{d(on)}$		25		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t _r		40		20
Turn-Off Delay Time	$R_G = 3.3\Omega$	$t_{d(off)}$		85		nS
Turn-Off Fall Time		t _f		45		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	V _{SD}	-	0.8	1.3	V
Reverse Recovery Time	I _S = 30A, T _J =25 °C dI/dt = 100A/us	t _{fr}		120		nS
Reverse Recovery Charge		Q _{fr}		160		nC

Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
 Rθ_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

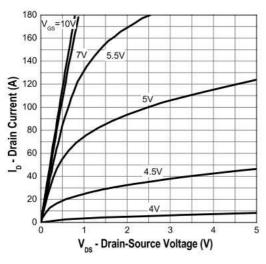


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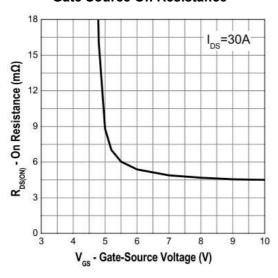


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

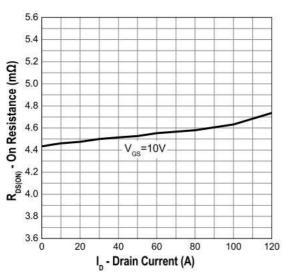
Output Characteristics



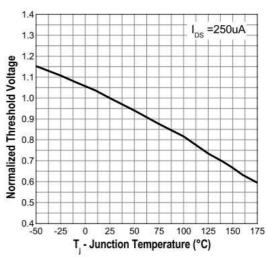
Gate Source On Resistance



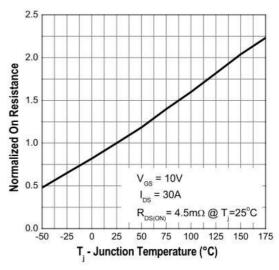
Drain-Source On-Resistance



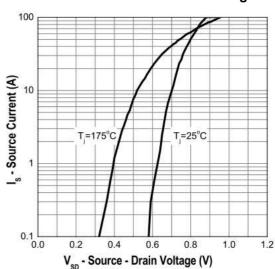
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward Voltage



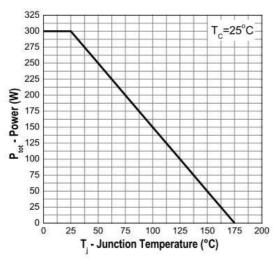


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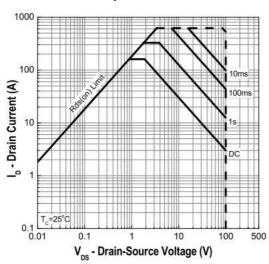


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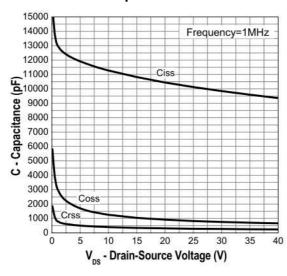




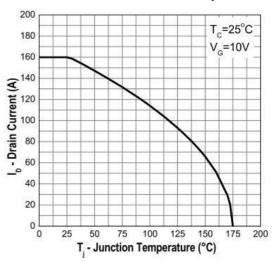
Safe Operation Area



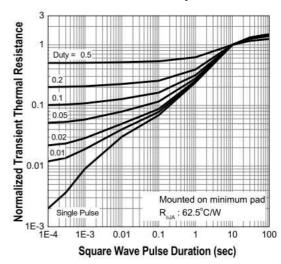
Capacitance



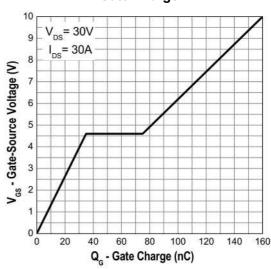
Drain Current vs. Junction Temperature



Transient Thermal Impedance



Gate Charge

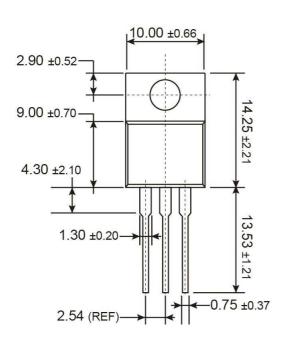


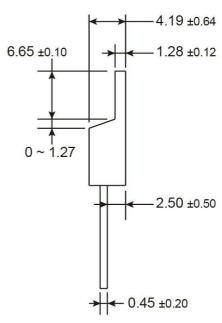






TO-220 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep,

J=Oct, K=Nov, L=Dec)

L = Lot Code



TSM160N10 100V N-Channel Power MOSFET

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